CS-02-068

IFW

August 5, 2004

To: Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Attn: Art Unit 2826 - Victor A. Mandala

From: George O. Saile, Reg. No. 19,572

28 Davis Avenue

Poughkeepsie, N. Y., 12603

Subject: | Serial No.: 10/628,913 07/29/03 |

Yeen Tat Chan et al.

METHOD OF FORMING A PARTIALLY DEPLETED SILICON ON INSULATOR (PDSOI) TRANSISTOR WITH A PAD LOCK BODY EXTENSION

|_ Art Group: 2826 Victor A. Mandala_|

RESPONSE TO RESTRICTION REQUIREMENT

This is in response to the Restriction or Election Requirement in the Office Action dated 07/23/04. In that Office Action, restriction was required to one of two stated

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on August 9 , 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date 8/9/04

Inventions under 35 U.S.C. 121. The Inventions stated are Group I - Claims 23-44 to a mosfet device structure, classified in Class 257, subclass 347 and Group II - Claims 1-22 to a process, classified in Class 438, subclass 149.

Applicant provisionally elects to be examined the Invention described by the Examiner as Group II - Claims 1-22 drawn to a process classified in Class 438, subclass 149. This election is made with traverse of the requirement under 37 C.F.R.1.143 for the reasons given in the following paragraphs.

The Examiner is respectfully requested to reconsider the Requirement for Restriction given in the Office Action. The Examiner gives the reason for the distinctness of the two inventions as (1) that the process as claimed can be used to make other and materially different products or (2) that the product as claimed can be made by another and materially different process (MPEP 806.05(f)). However, upon reading the product Claims against the process Claims one can readily see that the product Claims are directed to "a MOSFET device structure" and the process Claims are directed to "a method of forming a metal oxide semiconductor field effect transistor (MOSFET) device on a semiconductor substrate", it is necessary to obtain claims in both the product and method claim language. The method Claims necessarily use the product and vice versa. The field of search must necessarily cover both the method

class/subclass 438/149 and products class 257/347 in addition to other related Classes and subclasses to provide a complete and adequate search. The fields of search for the Group I and Group II inventions are clearly and necessarily co-extensive. The Examiner's suggestion that "In the instant case the device is made by forming the silicon layer and then forming an insulator filled, shallow trench isolation regions in the silicon layer as in claim 1 and as in claim 12, forming shallow trench shapes in said silicon layer. The device could be made by selectively depositing the silicon layer on the insulsting layer by having multiple silicon layers on the same level and separated by gaps as for claim 1, which would result in materially the same device and for claim 12, the trenches could be formed by selective depositing of the silicon, which also results in materially the same device," is very speculative and really has nothing to do with the Claims as presented in this Patent Application. Further, it is respectfully suggested that these reasons are insufficient to place the additional cost of a second Patent Application upon the Applicants. Therefore, it is respectfully requested that the Examiner withdraw this restriction requirement for these reasons.

Withdrawal of the Restriction Requirement and the Allowance of the present Patent Application is requested.

Sincerely,

Stephen B. Ackerman, Reg. #37761